

ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18

Stylesheet Version v18.0

Title of Invention

MAGNETIC RANDOM ACCESS MEMORY AND METHOD OF
FABRICATING THEREOF

Application Number : 10/604533

Confirmation Number: 7-29-03

First Named Applicant: William Wille

Attorney Docket Number: FIS920020132US1

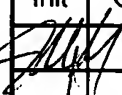

Art Unit: 2813

Examiner:

Search string: (5695810 or 5804458 or 5920500 or 5936293 or 6147900 or 6165803 or 6351408
or 6365419 or 6381170 or 6396735 or 6048739).pn

US Patent Documents

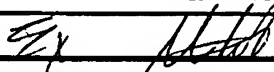
Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
	1	5695810	1997-12-09	Dubin, et al.			
	2	5804458	1998-09-08	Tehrani, et al.			
	3	5920500	1999-07-06	Tehrani, et al.			
	4	5936293	1999-08-10	Parkin			
	5	6147900	2000-11-14	Pohm			
	6	6165803	2000-12-26	Chen, et al.			
	7	6351408	2002-02-26	Schwarzl, et al.			
	8	6365419	2002-04-02	Durlam, et al.			
	9	6381170	2002-04-30	Prinz			
	10	6396735	2002-05-28	Michijima, et al.			
	11	6048739	2000-04-11	Hurst, et al.			

Signature

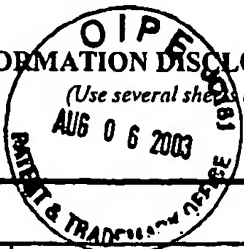
Examiner Name

Date



12/10/04

INFORMATION DISCLOSURE CITATION
(Use several sheets if necessary)



Docket Number (Optional) FIS920020132US1	Application Number NYA
Applicant(s) NUETZEL ET AL.	
Filing Date NYA	Group Art Unit NYA 2813

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

1	L. G. Svendsen, T. Osaka, I. Koiwa, and H. Sawai; "Chemically Deposited Ni-P and Ni-P-W Layers Investigated by Means of Rutherford Backscattering Spectrometry;" J. Electrochem. Soc.: SOLID-STATE SCIENCE AND TECHNOLOGY Vol. 130 No. 11, November 1983, pages 2255-2259
2	K. K. H. Wong, S. Kaja, P. W. DeHaven; "Metallization By Plating for High-Performance Multichip Modules," IBM Research Development, Vol. 42, No. 5, September 1998; pages 587 - 596.

EXAMINER <i>Ex</i> <i>[Signature]</i>	DATE CONSIDERED <i>12/11/04</i>
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION

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Docket Number (Optional)

FIS920020132US1

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NUETZEL ET AL.

Filing Date

NYA

Group Art Unit

NYA

*EXAMINER

INITIAL

OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

L.A. D'Asaro, J. V. DiLorenzo, and H. Fukui; "Improved Performance of GaAs Microwave Field-Effect Transistors with Low Inductance Via Connections Through the Substrate;" IEEE Transactions on Electron Devices, Vol. ED-25, No. 10, October 1978; pages 1218 - 1221.

T. Ishikawa, K. Okaniwa, M. Komaru, K. Kosaki, and Y. Mitsui; "A High-Power GaAs FET Having Buried Plated Heat Sink for High-Performance MMIC's" IEEE Transactions on Electron Devices, Vol. 41, No. 1; January 1994; pages 3 - 9

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